

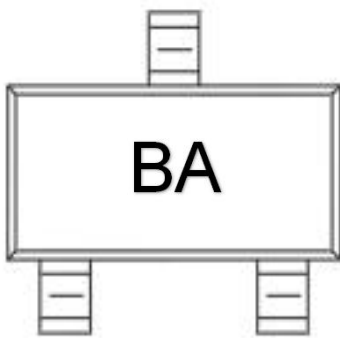


SHENZHEN MENGKE ELECTRONICS TECHNOLOGY CO.,LTD
SOT-23 Plastic-Encapsulate Transistors

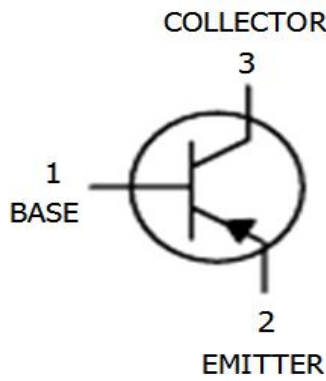
2SA1015

TRANSISTOR (PNP)

MARKING:

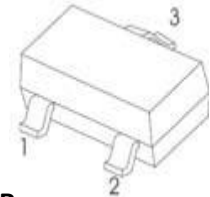


Equivalent Circuit:



SOT-23

- 1.BASE
- 2.EMITTER
- 3.COLLECTOR



FEATURES:

- ※ High voltage and high current
- ※ Excellent hFE Linearity
- ※ Complementary to C1815

MAXIMUM RATINGS (Ta=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	VCBO	-50	V
Collector-Emitter Voltage	VCEO	-50	V
Emitter-Base Voltage	VEBO	-5	V
Collector Current	IC	-150	mA
Collector Power Dissipation	PC	200	mW
Thermal Resistance From Junction To Ambient	RθJA	625	°C/W
Junction Temperature	Tj	150	°C
Storage Temperature	Tstg	-55~+150	°C



ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Collector-base breakdown voltage	V(BR)CBO	IC= -100μA, IE=0	-50			V
Collector-emitter breakdown voltage	V(BR)CEO	IC= -0.1mA, IB=0	-50			V
Emitter-base breakdown voltage	V(BR)EBO	IE=-100μA, IC=0	-5			V
Collector cut-off current	ICBO	VCB=-50 V , IE=0			-0.1	μA
Collector cut-off current	ICEO	VCB=-50V , IE=0			-1	μA
Emitter cut-off current	IEBO	VEB= -5V , IC=0			-0.1	μA
DC current gain	hFE	VCE=-6V, IC= -2mA	130		400	
	hFE	VCE=-6V, IC= -0.2mA	70			
Collector-emitter saturation voltage	VCE(sat)	IC=-100 mA, IB= -10mA			-0.3	V
Base-emitter saturation voltage	VBE(sat)	IC=-100 mA, IB= -10mA			-1.1	V
Transition frequency	fT	VCE=-10V, IC= -1mA f=30MHz	80			MHz
Collector Output Capacitance	Cob	VCB=-10V, IE= 0 f=1MHz			7	pf
Noise Figure	NF	VCE=-6V, IC= -0.1mA Rg=10kΩ; f=1kHz			6	dB

CLASSIFICATION OF hFE

Rank	L	H
Range	130-200	200-400



TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

